



### 歪み制御化学抵抗性ガスセンサーとその応用

Strain-controlled chemiresistive gas sensors and their applications

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2024年度中国人留学生研究奨励賞 授賞式並びに研究発表会

(2025/1/10, 東京)

Chap. 1 Demand for highly-sensitive and selective 2/36 gas sensors for health monitoring

Aged society → Rising healthcare burdens → Cost-effective medical method



with selectivity is required.

[1] X. Zhou et al. J. Mater. Chem. B, vol. 8, no. 16, pp. 3231–3248, 2020. [2] Gholizadeh, et al. Microsyst Nanoeng 3, 17022, 2017.

### Chap. 1 Chemiresistive gas sensors: compact, 3/36 affordable potential for long-term health monitoring

#### Traditional GC-MS



- Good sensitivity & selectivity
- Expensive and bulky
- Requires specialized training

#### Chemiresistive gas sensors

- ✓ High sensitivity
- ✓ Cost-effective
- ✓ Compact size

Make it possible

- ✓ Simplicity
- ✓ User-friendly, even for patients



### Their sensing mechanism and challenge

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### Previous study on methods

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to improve sensing performance



#### **Problems:**

- Only effective to specific kind of gas
- **D** Reduce the charge carrier mobility
- Requires extensive testing for suitable dopants

### Demands a high degree of control over functionalization

[1] AIP Advances 6, 025317 (2016) [2] Güntner, A. T.; et al. Prog. Energy Combust. Sci. 2022, 90, 100992.

#### Chap. 1 Previous study on the strain-dependent adsorption behaviour and research gap

- Strain engineering is popular but limited in gas sensing filed.
- Our lab recent work: strain can change the electrochemical properties of chemiresistive gas sensor [1~2]



# Improved over 30%

[1] Xiangyu Qiao et al. IMECE2020-23581. [2] Xiangyu Qiao et al. IMECE2023-112231.

20% strain -> Sensitivity Gap: How to understand the mechanism of strain modulated adsorption and whether this can be generalized across different sensing materials?

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### Proposal for strain-controlled chemoresistive

#### gas sensors from electronic band structure modulation



#### ✤ <u>My Proposal:</u>

- Strain can modulate materials electronic band structures (Dirac point position of graphene, CB/VB edge of WO<sub>3</sub>)
- → Their band alignment with molecular energy levels would be changed
- $\rightarrow$  The gas adsorption on these materials should be tuned

Establishment of a design guideline for strain-controlled chemiresistive gas sensors based on first-principles band alignment predictions, focusing on graphene and  $WO_3$ .

- 1. Develop an **accurate simulation framework** for understanding strain-controlled gas adsorption systems.
- Electronic structure analyze the effect of mechanical strain on gas adsorption behavior in graphene.
- 3. First-principles investigate how **structure defects** affect gas sensing performance in **strain-modulated graphene**.
- Extend the exploration of strain-controlled approach to WO<sub>3</sub>, as well as the effect of oxygen defects, comparing them with graphene for broader insights.

Chapter 1. Introduction and objective of this study

- Chapter 2. First-principles study of the effect of strain on gas adsorption in graphene
- Chapter 3. Electronic band structure investigation of the role of defect in strain-modulated graphene gas sensors
- Chapter 4. From graphene to WO<sub>3</sub>: exploring the design guideline for strain-controlled chemiresistive gas sensors (on-going...)
- Chapter 5. Summary and outlook

Chap. 2 First-principles study of the effect of strain <sup>10/36</sup> on gas adsorption in graphene



Understand the impact of **mechanical strain** on gas adsorption behavior in **graphene** from first-principles calculation

Key Requirements:

- 1. Establishing a simulation framework for evaluating the strain-modulated gas adsorption systems
- 2. Understanding the effect of strain on gas adsorption in graphene
- 3. Validating strain effects through comparison with experimental results

### Existing issues to develop a

Chap. 2

strain-controlled chemiresistive gas sensor

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Clarification of the adsorption-induced change of graphene's electrical properties



### Strategy and computational method



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#### Chap. 2 Computational models and key parameters



◆ Key parameters for the evaluation of gas adsorption behavior on graphene

(1) Adsorption energy,  $E_{ad}$ 

$$E_{ad} = E_{graphene with gas}$$
$$- E_{graphene}$$
$$- E_{gas molecular}$$
$$E_{ad} < 0$$
$$\Rightarrow adsorption$$





- ③ Charge density difference(CDD)
- $\Delta \rho = \rho_{graphene \ with \ gas}$   $\rho_{graphene}$   $\rho_{gas \ molecular}$ From the view of orbital interactions

# Variation of adsorption energy with applied strain

14/36

Chap. 2



Different gas species have different strain sensitivity

→ Can be used as an important factor to improve the selectivity

### Chap. 2 Variation of charge transfer under 15/36 the applied strain



Strain-induced change of charge transfer between  $NO_2$  and graphene is much larger than that on  $NH_3$ .

### Variation of band structure under the applied strain

16/36

Chap. 2



The effect of strain on the band structure of  $NO_2$  on graphene is more significant, while the effect on  $NH_3$  is almost neglected.

### Chap. 2 Mechanism discussion of strain-effect <sup>17/36</sup> on gas adsorption in graphene



Strain could shift graphene Dirac point, changing the energy difference between molecular HOMO/LUMO and Graphene's E-Fermi, thus tuning the binding between gas and graphene.

Chap. 2

### Validation by experiements



### Summary of chapter 2.



- 1. Without strains, the calculated results show good consistent with both simulation and experiment work, confirming the reliability of the established simulation framework.
- 2. The strain effect was found to be gas-species dependent, with a significantly larger effect on  $NO_2$  compared to  $NH_3$ , explained by band structure analysis.
- **3.** Our experimental validation further supports the simulated trend/prediction.

Meng Yin et al. Diam. Relat. Mat., 2024, 142, 110822

Chap. 3 Role of defects in strain-modulated 20/36 graphene gas sensors



Key Requirements:

- 1. Understanding the effects of common structure defects (Stone-wales, Single vacancy) on graphene.
- 2. Analyze the gas adsorption behaviour of graphene in the presence of these defects.
- 3. Elucidation of mechanism of gas adsorption underlying considering both strain and defects.



Energÿ/eV

Energy/eV

SW defect introduce states above ~0.5 eV near E-Fermi, while SV graphene exhibit more pronounced defect states at E-Fermi.

[1] M. Datt Bhatt, H. Kim, G. Kim, Various defects in graphene: a review, RSC Adv. 12 (2022) 21520–21547.

### Enhanced NO<sub>2</sub> adsorption on defective graphene



Adsorption energy

$E_{ad} = E_{total} - E_{DG} - E_{gas}$				
Systems	Esys/eV	Eslab/eV	Egas/eV	Ead/eV
PG+NO <sub>2</sub>	-574.147	-555.518	-18.372	-0.257
SWG+NO <sub>2</sub>	-569.142	-549.719	-18.372	-1.050
SVG+NO <sub>2</sub>	-559.355	-538.613	-18.372	-2.370

 Both SWG and SVG exhibit enhanced NO<sub>2</sub> adsorption than that on PG.

On SVG,  $NO_2 \rightarrow NO+O$  due to the presence of dangling bonds.

### Chap. 3 NO<sub>2</sub> adsorption on defective graphene <sup>23/36</sup> under uniaxial tensile strains

X-strains on PG/SWG/SVG+NO<sub>2</sub>



Under tensile strain along the X-direction, NO<sub>2</sub> binding was weakened on all surfaces, with SVG transitioning from dissociative to molecular adsorption.

### Chap. 3 Variation of NO<sub>2</sub> adsorption on defective <sup>24/36</sup> graphene under different strains



The adsorption of  $NO_2$  on PG and SWG shows a similar trend in response to strain, while SVG exhibits a dependence on the direction of the applied strain.



- The strain effect on NO<sub>2</sub> adsorption is influenced by dangling bonds at defect sites, with PG/SWG following the Chap. 2 mechanism.
- While SVG exhibits strain-dependent spin density variations, affecting its sensing capabilities.

### Summary of chapter 3.



- 1. Both Stone-Wales (SW) and single-vacancy (SV) defects enhance  $NO_2$  sensing, with SVG facilitating  $NO_2$  dissociation due to dangling bonds.
- Strain effects were systematically studied, showing similar trends for PG/SWG but direction-dependent behavior for SVG.
- 3. The strain-controlled gas sensing mechanism for graphene was refined and extended based on the model proposed in Chapter 2.

### Proposal for strain-controlled chemoresistive

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#### gas sensors from electronic band structure modulation



 ✓ In graphene (special Dirac cone structure), strain can modulate the position of Dirac point → achieve molecular orbital matching modulation

Now, it is possible to generalize this mechanism to more general semiconductor type electronic structures (WO3) ?

Chap. 4 From graphene to WO<sub>3</sub>: exploring band <sup>28/36</sup>

structure driven gas sensors via strain-controlled method

#### Objective

Extend the understanding of strain effects to WO<sub>3</sub> with oxygen vacancies, comparing its performance with graphene for broader insights.

### Expeirment

- Materials characteriation
  - Phase composition, XRD
  - Band gap measurement, Uv-vis
  - X-ray absorption fine structures
- Surface chemistry
  - In-situ DRIFTS
  - TPD
- Transduction
  - Kelvin probe
  - Operando work function measurement

### **DFT calculation**

#### Structure properties

- Fully relaxed geometry
- Simulated band structure

#### About surface

- Slab model
- The effect of oxygen vacancy
- Adosprion energy
- Electronic properties
  - Charge density difference
  - Band structure analysis
  - Work function

**Collaboration with HSL group at ETH Zurich** (9 month visiting and close teamwork)

HSL

Mr. Matteo D'Andria

Combustion-aerosol Synthesis of Metastable Nanocrystals for Molecular Sensing and Catalys

M. D'Andria<sup>1</sup>, T. Elias Abi-Ramia Silva<sup>1</sup>, E. Co

Prof. Andreas T. Güntner

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### Chap. 4 Material synthesis and characterisctis



- WO<sub>3</sub> was synthesized using Flame spray pyrolysis (FSP).
- XRD and TEM image indicated the fabricated WO<sub>3</sub> has high crystallinity.
- X-ray absorption fine structures  $\rightarrow$  a corner-sharing WO<sub>6</sub> octahedral structure.

# Chap. 4 31/36 Measured and DFT-1/2 calcualted bandgaps



Our measured bandgaps of WO<sub>3</sub> v.s. DFT calculated  $\rightarrow$  Good consistant with previous report, with the range of 2.6~3.2 eV <sup>[3]</sup>.

[1] Ferreria, L. G.; et al. Phys. Rev. B 2008, 78, 125116. [2] Americo, S.; et al. Electrochim. Acta 2021, 371, 137611. [3] Wang, F.; et al. J. Phys. Chem. C 2011, 115, 8345–8353.

### Chap. 4 Surface modelling and the effect of <sup>32/36</sup> oxygen vacancies



Partial charge density ( $E_{F-1}$  to  $E_F$ ) indicates that the electrons around Fermi level are distributed throughout the system as free electrons rather than localized states.

### Surface chemistry



The binding energy is appropriate and should lead to a decrease in measured resistivity when acetone (a reducing agent) interacts with  $WO_3$  (an n-type semiconductor)

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# Effect of strain on WO<sub>3</sub> and its gas sensing properties and further experimental validations (on-going...)



chemiresistive gas sensors based on first-principles band alignment predictions  $\rightarrow$  Lots of applications from earth to space





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## Thank you for your attention!

ご清聴ありがとうございました!

感谢各位的聆听!